

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max	$I_D$ Max $T_C = +25^\circ\text{C}$
60V	25m $\Omega$ @ $V_{GS} = 10\text{V}$	32A
	40m $\Omega$ @ $V_{GS} = 4.5\text{V}$	25A

## Description

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

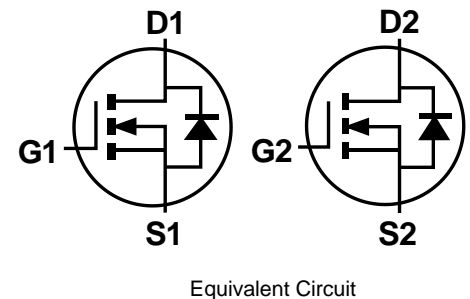
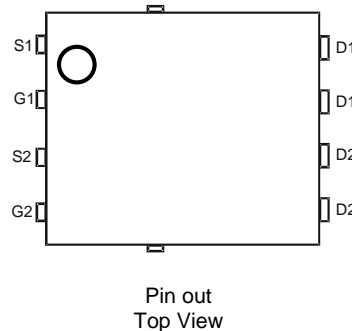
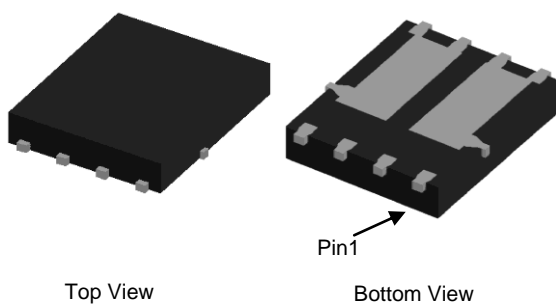
- Backlighting
- Power Management Functions
- DC-DC Converters

## Features and Benefits

- Rated to  $+175^\circ\text{C}$  – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low  $R_{DS(ON)}$  – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Complaint Part is Available Under Separate Datasheet ([DMNH6021SPDQ](#))**

## Mechanical Data

- Case: PowerDI<sup>®</sup>5060-8 (Type C)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)

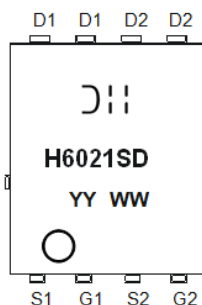


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMNH6021SPD-13	PowerDI5060-8 (Type C)	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  3. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



$\text{D}|||$  = Manufacturer's Marking  
 H6021SD = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Year (ex: 16 = 2016)  
 WW = Week (01 - 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V <sub>DSS</sub>	60	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	I <sub>D</sub>	T <sub>A</sub> = +25°C	8.2
		T <sub>A</sub> = +70°C	6.5
Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V	I <sub>D</sub>	T <sub>C</sub> = +25°C	32
		T <sub>C</sub> = +100°C	22
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	80	A
Maximum Continuous Body Diode Forward Current (Note 7)	I <sub>S</sub>	32	A
Avalanche Current, L = 0.1mH (Note 8)	I <sub>AS</sub>	35	A
Avalanche Energy, L = 0.1mH (Note 8)	E <sub>AS</sub>	64	mJ

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P <sub>D</sub>	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	Steady State	99
		t < 10s	53
Total Power Dissipation (Note 6)	P <sub>D</sub>	2.8	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	Steady State	54
		t < 10s	27
Thermal Resistance, Junction to Case (Note 7)	R <sub>θJC</sub>	2.2	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 9)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 9)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	—	3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	15	25	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 15A
		—	21	40		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 12A
Diode Forward Voltage	V <sub>SD</sub>	—	0.75	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 2.6A
<b>DYNAMIC CHARACTERISTICS</b> (Note 10)						
Input Capacitance	C <sub>ISS</sub>	—	1,143	—	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>OSS</sub>	—	168	—	pF	
Reverse Transfer Capacitance	C <sub>RSS</sub>	—	69	—	pF	
Gate Resistance	R <sub>G</sub>	—	2.1	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>G</sub>	—	20.1	—	nC	V <sub>DS</sub> = 30V, I <sub>D</sub> = 20A,
Total Gate Charge (V <sub>GS</sub> = 6V)	Q <sub>G</sub>	—	12	—	nC	
Gate-Source Charge	Q <sub>GS</sub>	—	4.3	—	nC	
Gate-Drain Charge	Q <sub>GD</sub>	—	5.5	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	4.4	—	ns	V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V, R <sub>G</sub> = 4.7Ω, I <sub>D</sub> = 20A
Turn-On Rise Time	t <sub>R</sub>	—	6.0	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	14.2	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	5.4	—	ns	
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	21.2	—	ns	IF = 20A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	15.2	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1 inch square copper plate.
  - Thermal resistance from junction to soldering point (on the exposed drain pad).
  - I<sub>AS</sub> and E<sub>AS</sub> rating are based on low frequency and duty cycles to keep T<sub>J</sub> = 25°C
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

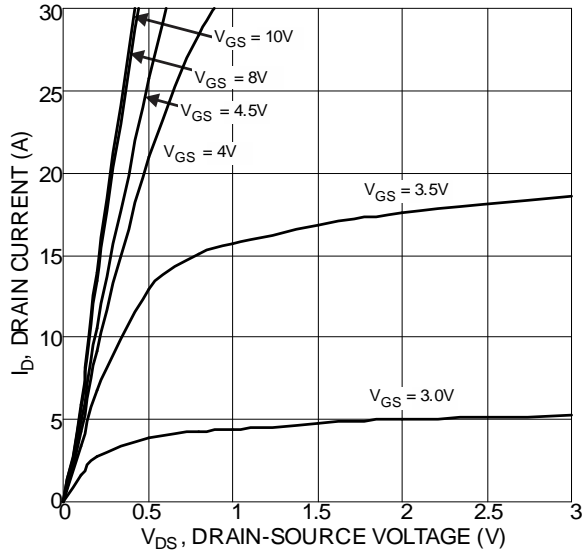


Figure 1 Typical Output Characteristic

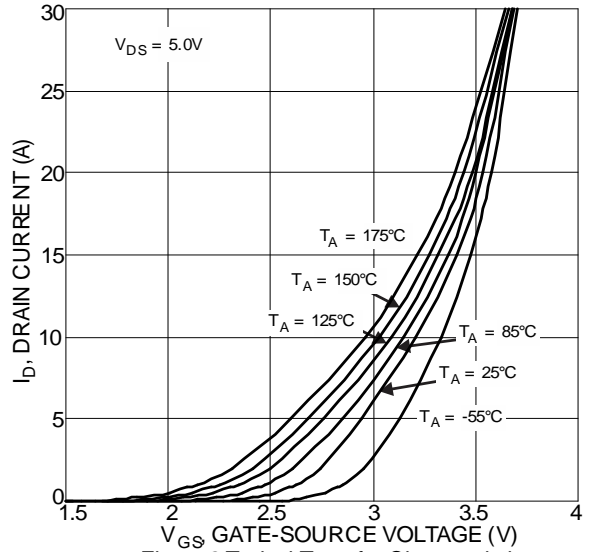


Figure 2 Typical Transfer Characteristics

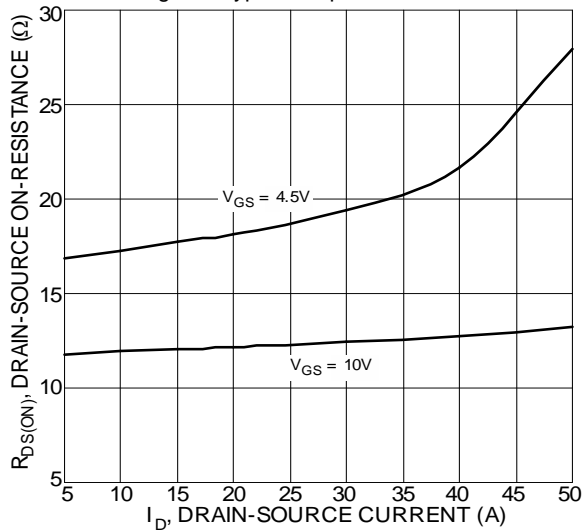


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

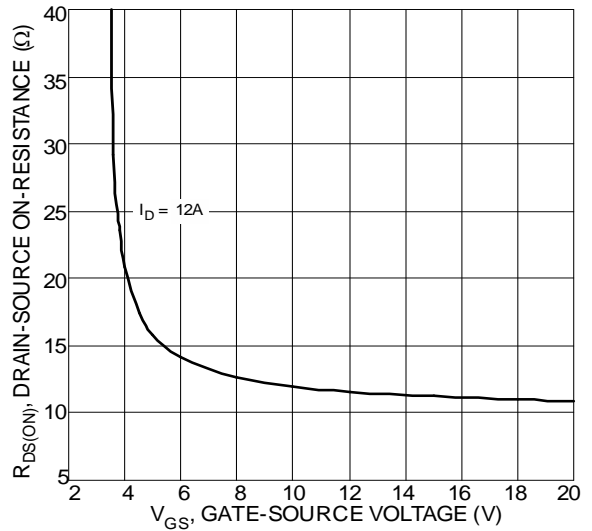


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

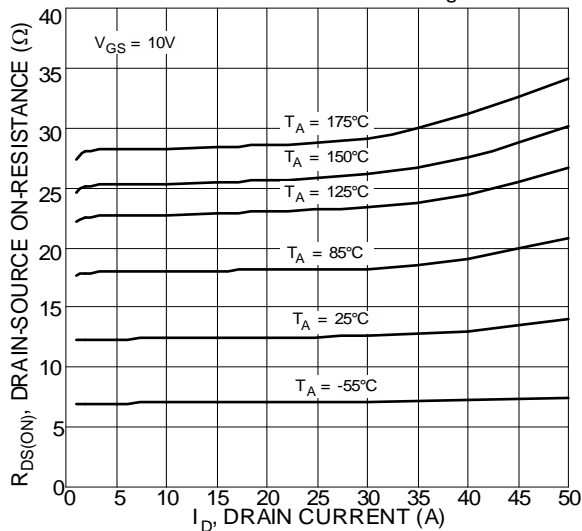


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

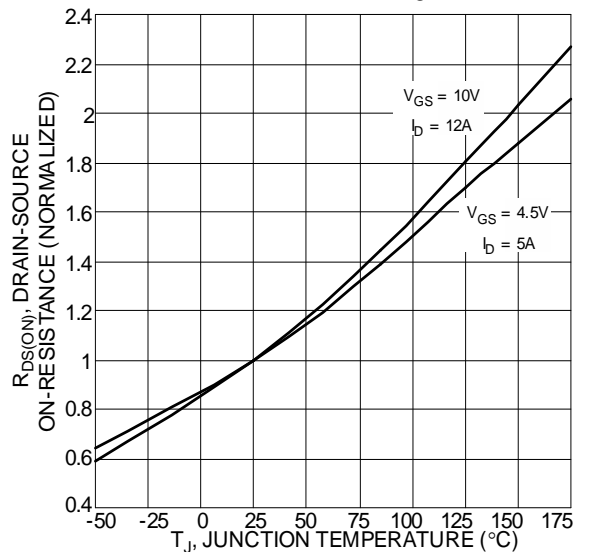


Figure 6 On-Resistance Variation with Temperature

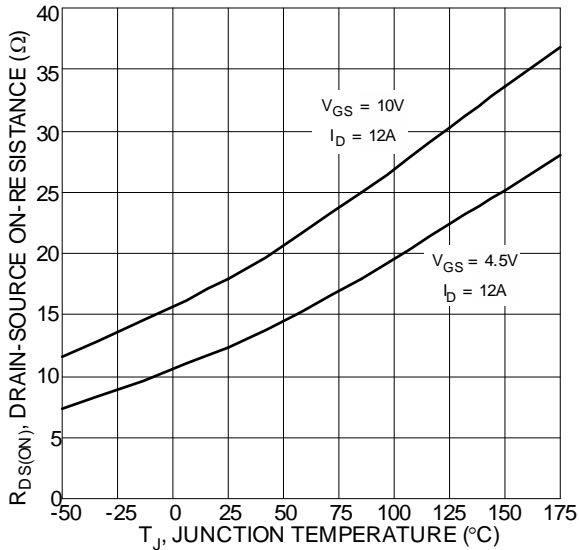


Figure 7 On-Resistance Variation with Temperature

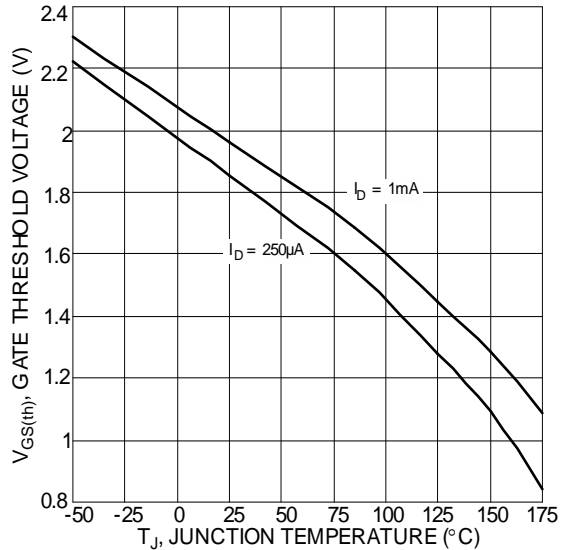


Figure 8 Gate Threshold Variation vs. Ambient Temperature

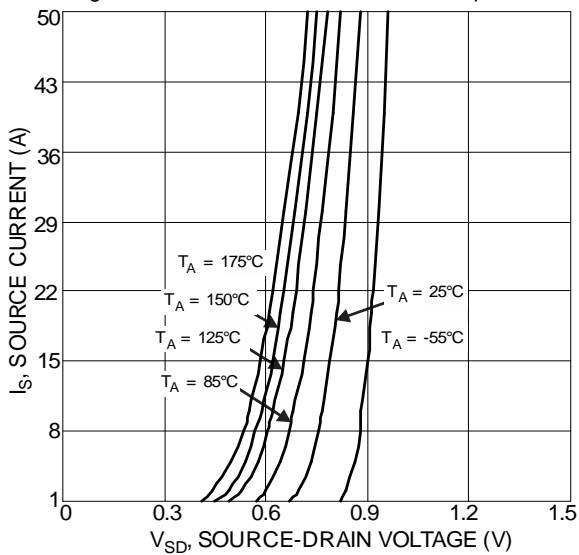


Figure 9 Diode Forward Voltage vs. Current

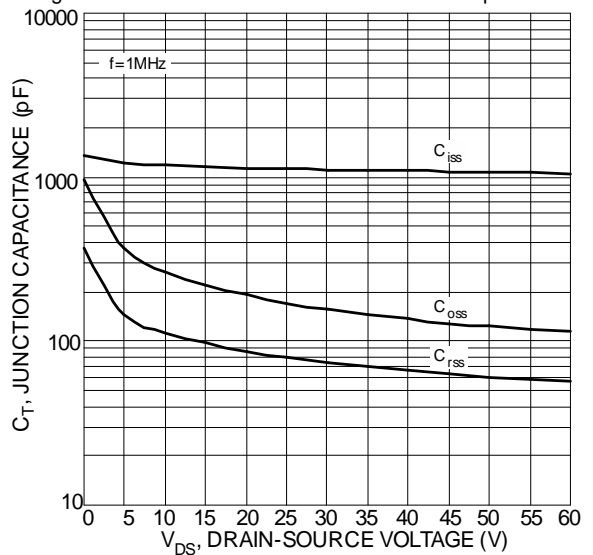


Figure 10 Typical Junction Capacitance

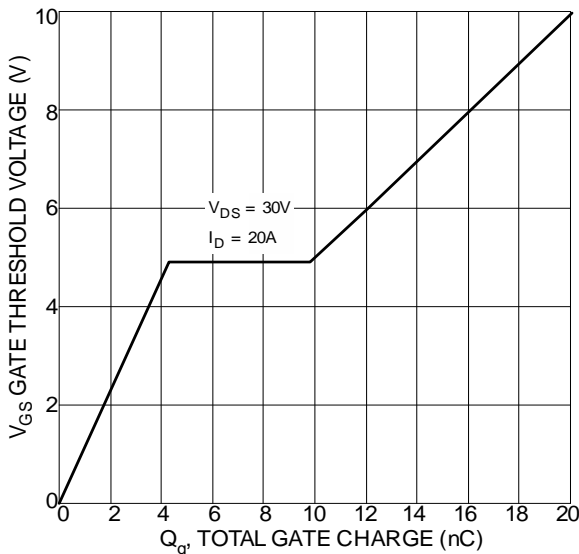


Figure 11 Gate Charge

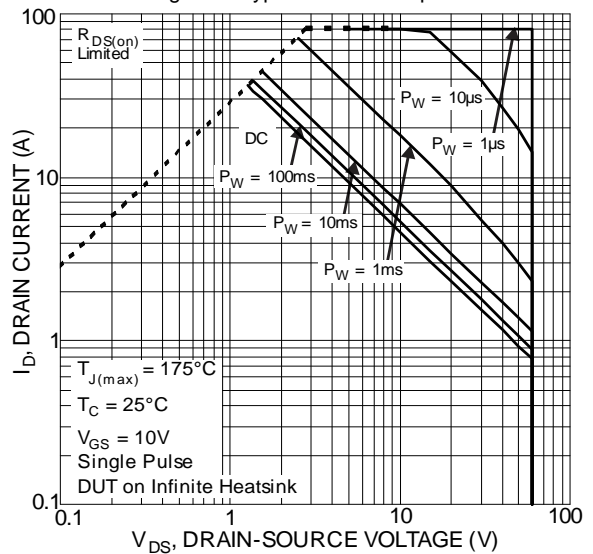
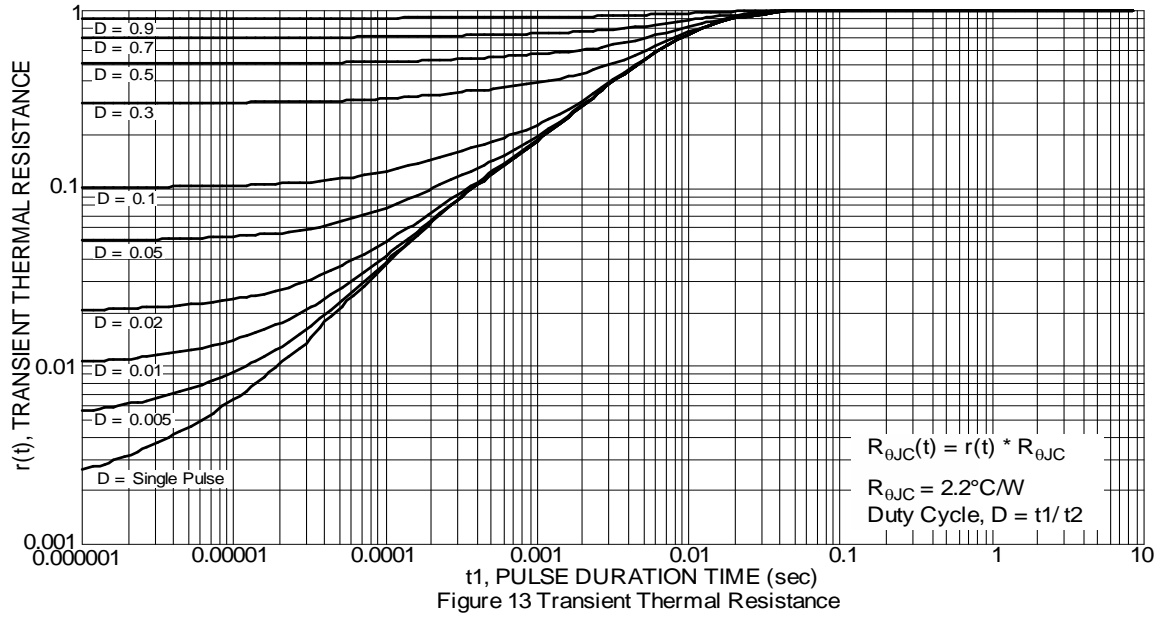


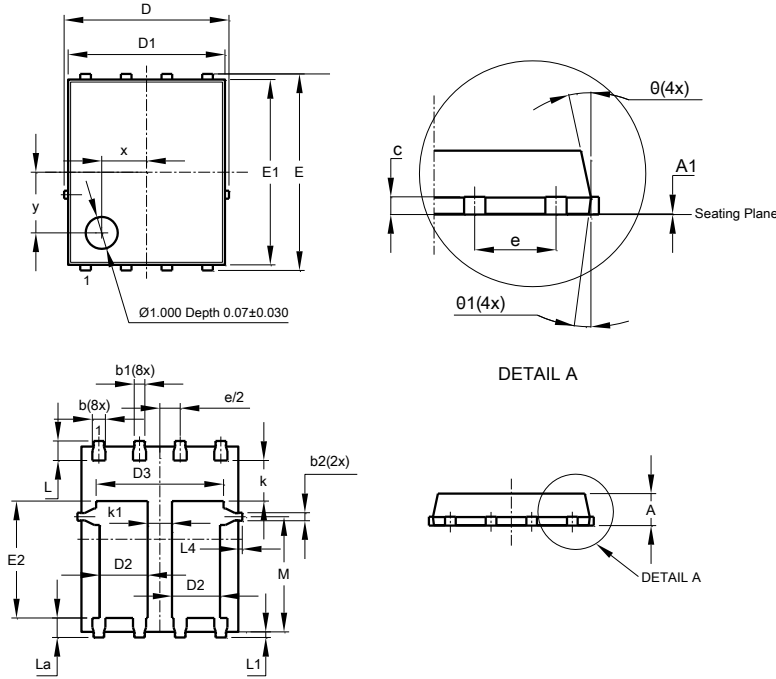
Figure 12 SOA, Safe Operation Area



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI5060-8 (Type C)**

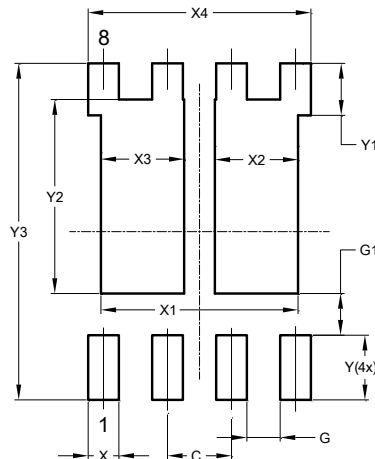


PowerDI5060-8 (Type C)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	0.02
b	0.33	0.51	0.41
b1	0.300	0.366	0.333
b2	0.20	0.35	0.25
c	0.23	0.33	0.277
D	5.15 BSC		
D1	4.85	4.95	4.90
D2	1.40	1.60	1.50
D3	-	-	3.98
E	6.15 BSC		
E1	5.75	5.85	5.80
E2	3.56	3.76	3.66
e	1.27BSC		
k	-	-	1.27
k1	0.56	-	-
L	0.51	0.71	0.61
La	0.51	0.71	0.61
L1	0.05	0.20	0.175
L4	-	-	0.125
M	3.50	3.71	3.605
x	-	-	1.400
y	-	-	1.900
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI5060-8 (Type C)**



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	3.910
X2	1.650
X3	1.650
X4	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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